Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D T_C = +25°C
1200V	43mΩ @ V_{GS} = 15V	70.5A

Features and Benefits

- Low On-Resistance
- High BV_{DSS} Rating for Power Application
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMWSH120H43SM4Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

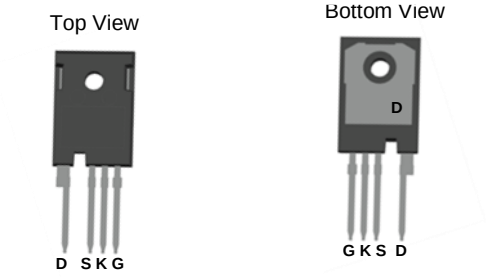
This SiC MOSFET is designed to minimize the on-state resistance yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- EV high-power DC-DC converters
- EV charging systems
- AC-DC traction inverters
- Solar inverters
- Automotive motor drivers

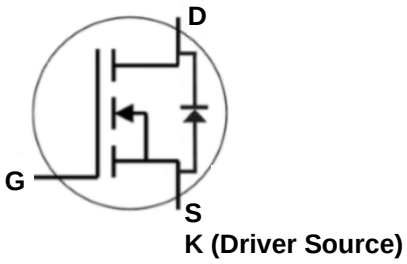
Mechanical Data

- Package: TO247-4
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 6.6 grams (Approximate)

TO247-4 Standard



Pin Configuration



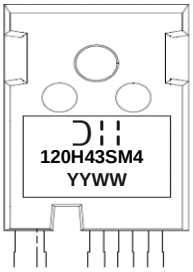
Internal Schematic

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMWSH120H43SM4Q	TO247-4 Standard	30 Pieces	Tube

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



= Manufacturer's Marking
120H43SM4 = Product Type Marking Code
YYWW or YYWW = Date Code Marking
YY or YY = Last Two Digits of Year (ex: 24 = 2024)
WW or WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	1200	V
Gate-Source Voltage		V_{GSS}	+19/-8	V
Gate-Source Voltage (Recommended Operating Values)		V_{GSS}	+15/-4	V
Continuous Drain Current (Notes 5, 6)	T_C = +25°C T_C = +100°C	I_D	70.5 49.8	A
Continuous Diode Forward Current (Note 5)		I_S	63	A
Pulsed Source Current (Pulse Width t_P Limited by $T_{J\,Max}$) (Note 5)		I_{SM}	151	A
Pulsed Drain Current (Pulse Width t_P Limited by $T_{J\,Max}$) (Note 5)		I_{DM}	151	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_C = +25°C	P_D	320	W
	T_C = +100°C		160	
Thermal Resistance, Junction to Ambient (Note 7)		$R_{\theta JA}$	29.4	°C/W
Thermal Resistance, Junction to Case (Note 5)		$R_{\theta JC}$	0.47	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	1200	—	—	V	V_{GS} = 0, I_D = 100µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	50	µA	V_{DS} = 1200V, V_{GS} = 0
Gate-Source Leakage	I_{GSS}	—	—	±250	nA	V_{GS} = +15/-4V, V_{DS} = 0
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.8	2.5	3.6	V	V_{DS} = V_{GS}, I_D = 11.5mA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	33	43	mΩ	V_{GS} = 15V, I_D = 40A
Diode Forward Voltage	V_{SD}	—	4.0	—	V	V_{GS} = -4V, I_S = 20A
Transconductance	gfs	—	8.9	—	S	V_{DS} = 20V, I_D = 40A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	2204	—	pF	V_{GS} = 0, V_{DS} = 1000V V_{AC} = 25mV, f = 1MHz
Output Capacitance	C_{oss}	—	106	—		
Reverse Transfer Capacitance	C_{rss}	—	6.6	—		
C_{oss} Stored Energy	E_{oss}	—	65	—	µJ	
Turn-On Switching Energy (Body Diode Forward)	E_{ON}	—	581	—	µJ	V_{GS} = -4V/+15V, V_{DS} = 800V R_g = 5Ω, I_D = 40A, L = 157µH
Turn-Off Switching Energy (Body Diode Forward)	E_{OFF}	—	245	—		
Gate Resistance	R_g	—	1.4	—	Ω	V_{AC} = 100mV, f = 1MHz
Total Gate Charge	Q_g	—	114	—	nC	V_{GS} = -4V/+15V, V_{DS} = 800V I_D = 40A
Gate-Source Charge	Q_{gs}	—	40.9	—		
Gate-Drain Charge	Q_{gd}	—	38.7	—		
Turn-On Delay Time	$t_{D(ON)}$	—	15.8	—	ns	V_{GS} = -4V/+15V, V_{DD} = 800V R_g = 5Ω, I_D = 40A Inductive Load
Turn-On Rise Time	t_R	—	37.3	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	31.3	—		
Turn-Off Fall Time	t_F	—	8.9	—		
Body Diode Reverse-Recovery Time	t_{RR}	—	21.4	—	ns	V_{GS} = -4V, V_{DS} = 800V I_D = 40A, di/dt = 1500A/µs
Body Diode Reverse-Recovery Charge	Q_{RR}	—	208	—	nC	
Body Diode Reverse-Recovery Current	I_{RRM}	—	16.1	—	A	

Notes:
5. Device mounted on an infinite heatsink.
6. Drain current limited by maximum junction temperature.
7. Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to production testing.

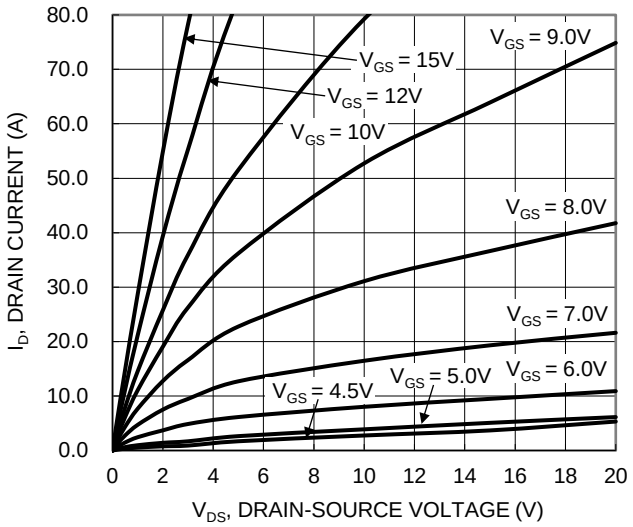


Figure 1. Typical Output Characteristic

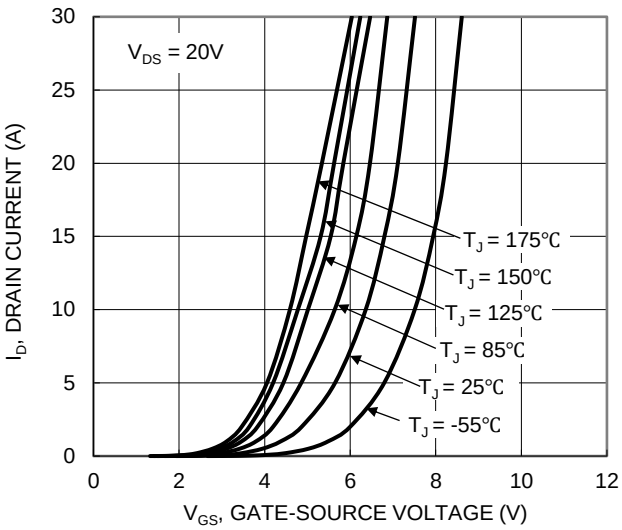


Figure 2. Typical Transfer Characteristic

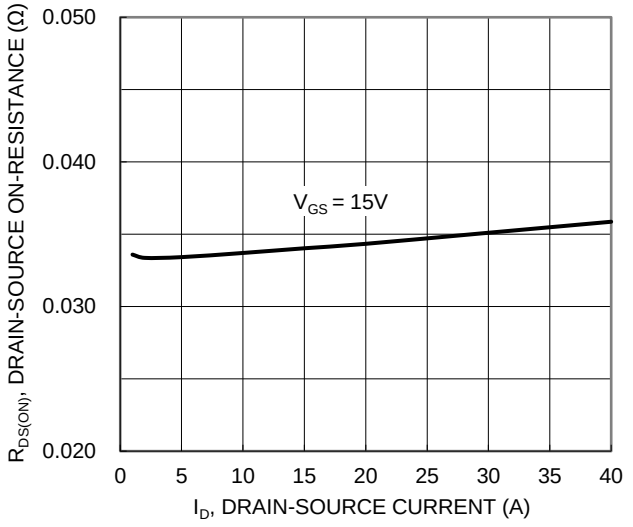


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

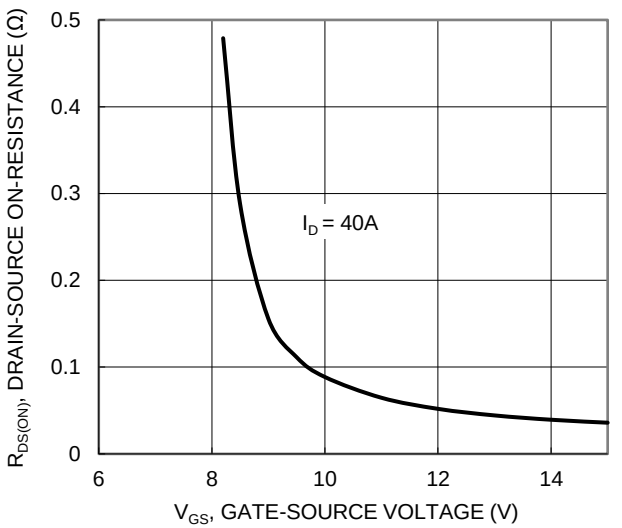


Figure 4. Typical Transfer Characteristic

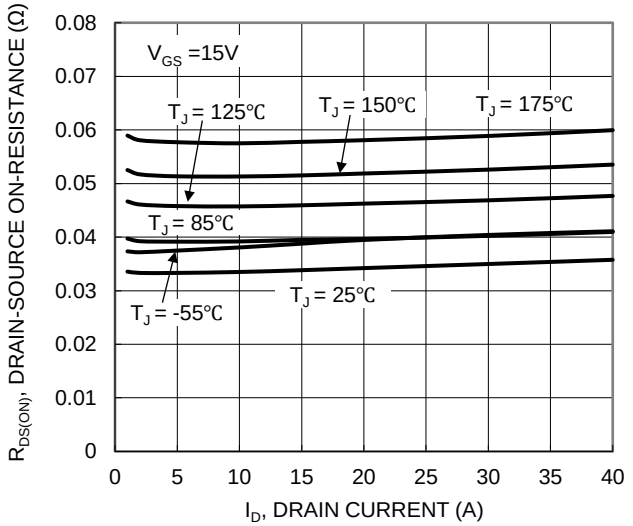


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

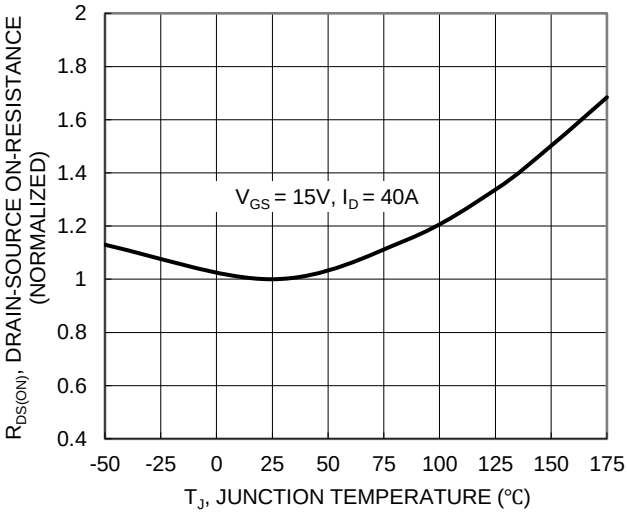


Figure 6. On-Resistance Variation with Junction Temperature

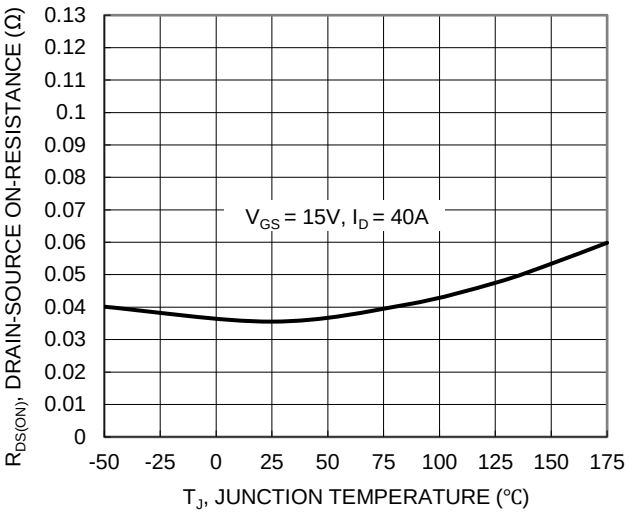


Figure 7. On-Resistance Variation with Junction Temperature

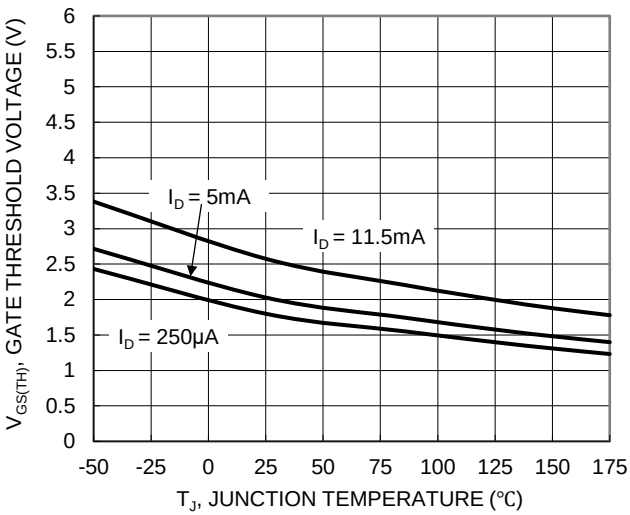


Figure 8. Gate Threshold Variation vs. Junction Temperature

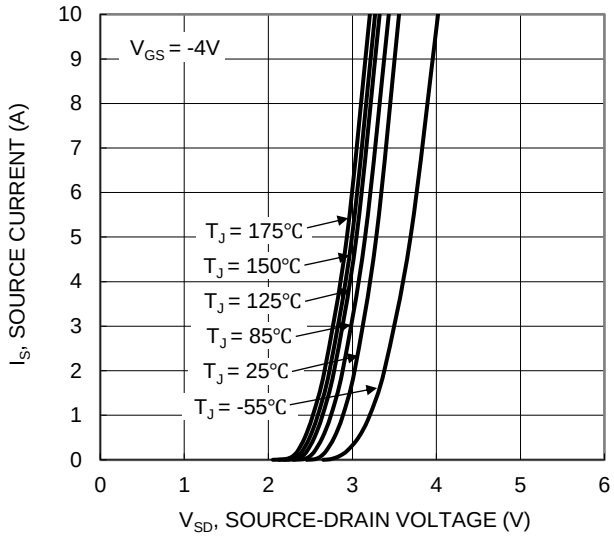


Figure 9. Diode Forward Voltage vs. Current

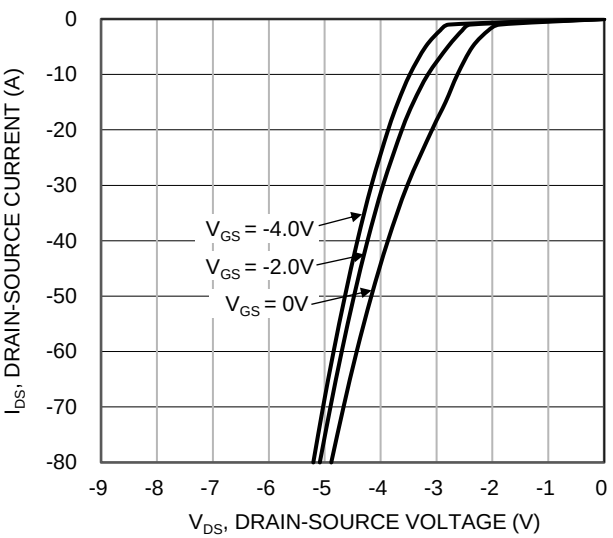


Figure 10. Body Diode Characteristic at 25℃

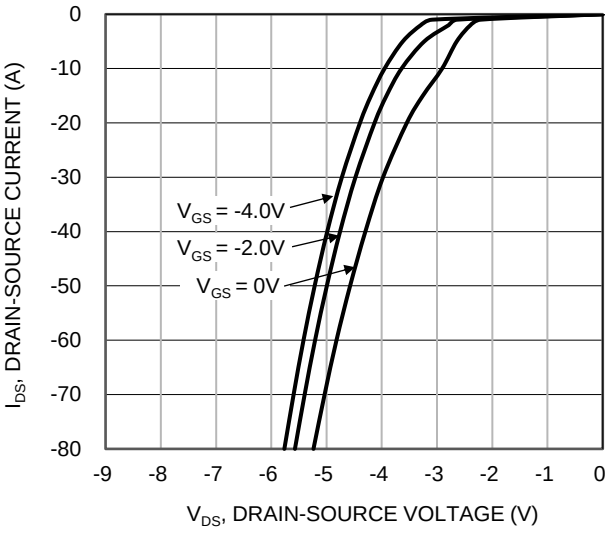


Figure 11. Body Diode Characteristic at -55℃

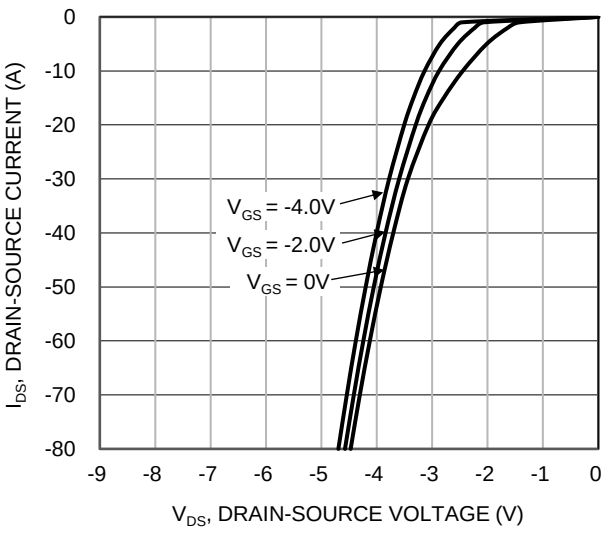


Figure 12. Body Diode Characteristic at 175℃

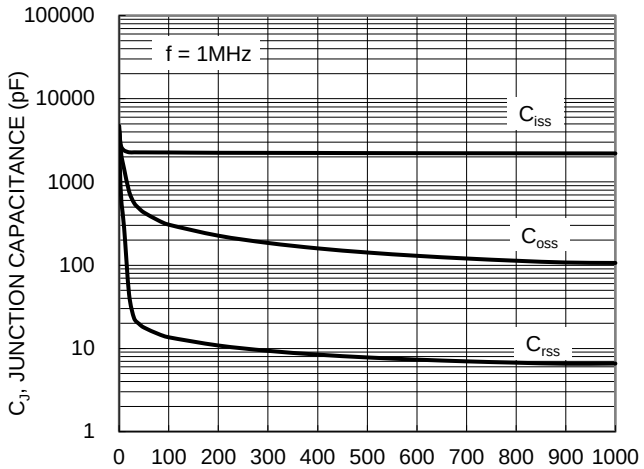


Figure 13. Typical Junction Capacitance

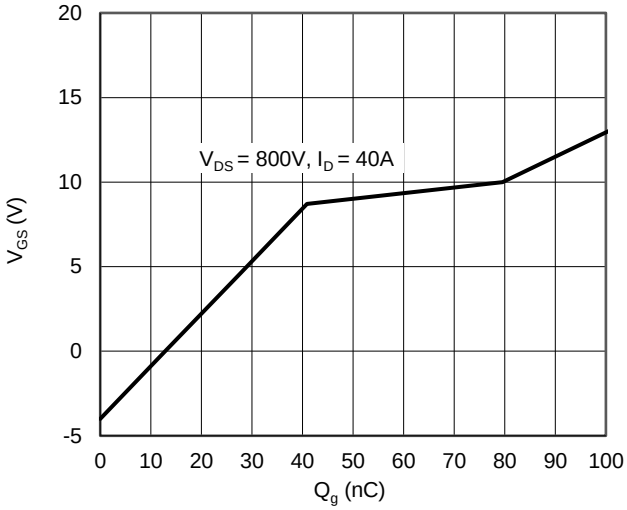


Figure 14. Gate Charge

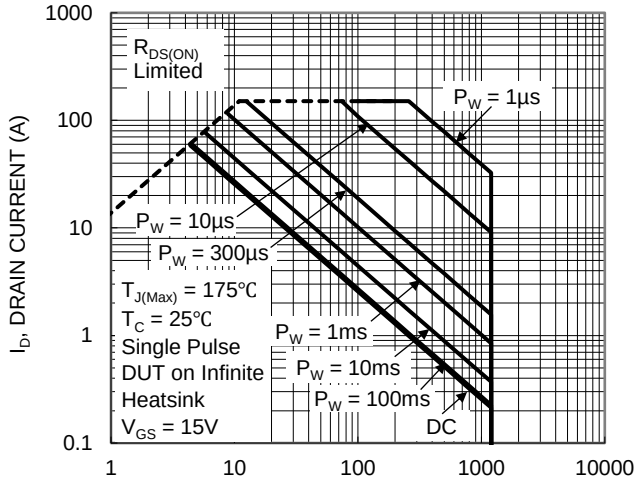


Figure 15. SOA, Safe Operation Area

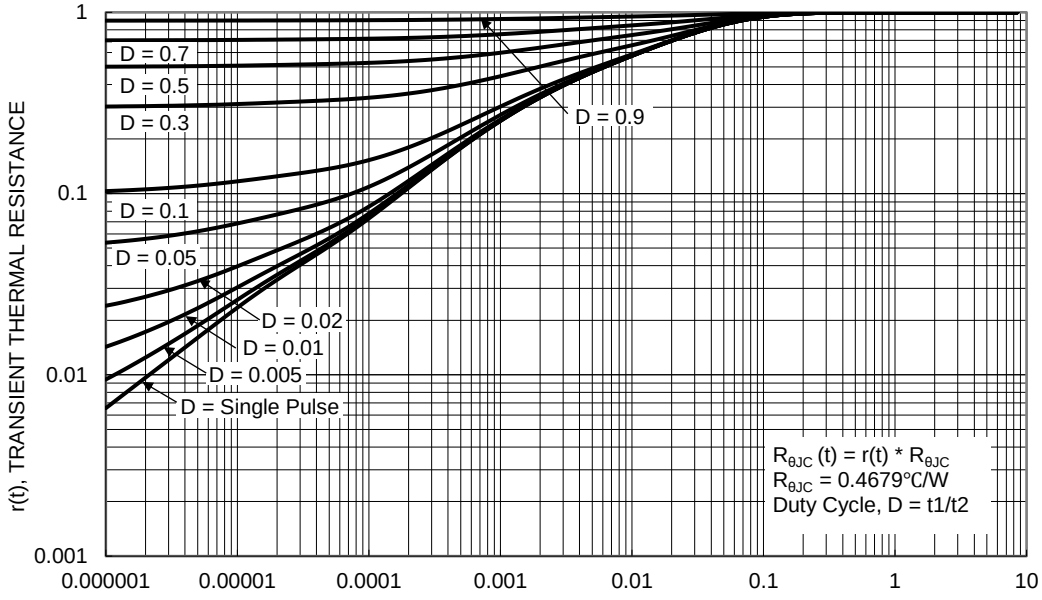
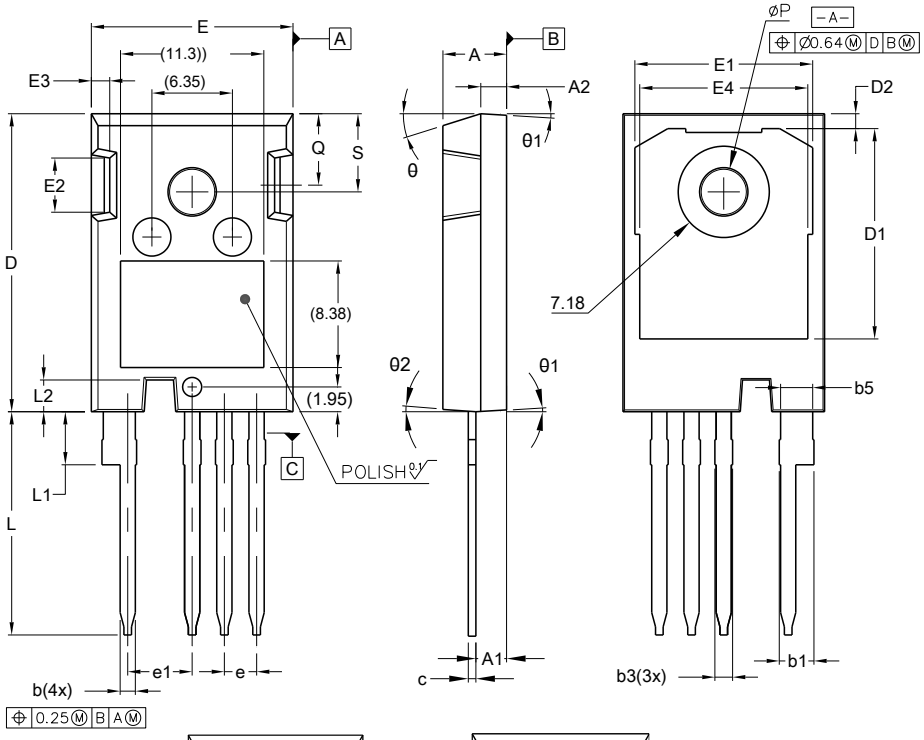


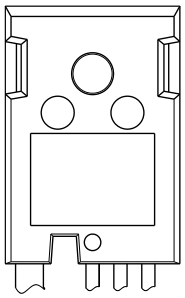
Figure 16. Transient Thermal Resistance

Package Outline Dimensions

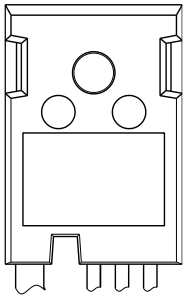
Please see http://www.diodes.com/package-outlines.html for the latest version.

TO247-4 Standard





OPTION A
(TOP VIEW)



OPTION B
(TOP VIEW)

TO247-4 Standard		
Dim	**Min**	**Max**
A	4.83	5.21
A1	2.29	2.54
A2	1.91	2.16
b	1.07	1.33
b1	2.39	2.94
b3	1.07	1.60
b5	2.39	2.69
c	0.55	0.68
D	23.30	23.60
D1	16.25	17.65
D2	0.95	1.25
E	15.75	16.30
E1	13.10	14.15
E2	3.68	5.10
E3	1.00	1.90
E4	12.38	13.43
e	2.54 BSC	
e1	5.08 BSC	
L	17.31	17.82
L1	3.97	4.37
L2	2.35	2.65
ØP	3.51	3.65
Q	5.49	6.00
S	6.04	6.30
θ	17.5°- 20° REF	
θ1	3.5°- 5° REF	
θ2	4°- 5° REF	
All Dimensions in mm		

IMPORTANT NOTICE

1. DIODES INCORPORATED (Diodes) AND ITS SUBSIDIARIES MAKE NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO ANY INFORMATION CONTAINED IN THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

2. The Information contained herein is for informational purpose only and is provided only to illustrate the operation of Diodes' products described herein and application examples. Diodes does not assume any liability arising out of the application or use of this document or any product described herein. This document is intended for skilled and technically trained engineering customers and users who design with Diodes' products. Diodes' products may be used to facilitate safety-related applications; however, in all instances customers and users are responsible for (a) selecting the appropriate Diodes products for their applications, (b) evaluating the suitability of Diodes' products for their intended applications, (c) ensuring their applications, which incorporate Diodes' products, comply the applicable legal and regulatory requirements as well as safety and functional-safety related standards, and (d) ensuring they design with appropriate safeguards (including testing, validation, quality control techniques, redundancy, malfunction prevention, and appropriate treatment for aging degradation) to minimize the risks associated with their applications.

3. Diodes assumes no liability for any application-related information, support, assistance or feedback that may be provided by Diodes from time to time. Any customer or user of this document or products described herein will assume all risks and liabilities associated with such use, and will hold Diodes and all companies whose products are represented herein or on Diodes' websites, harmless against all damages and liabilities.

4. Products described herein may be covered by one or more United States, international or foreign patents and pending patent applications. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks and trademark applications. Diodes does not convey any license under any of its intellectual property rights or the rights of any third parties (including third parties whose products and services may be described in this document or on Diodes' website) under this document.

5. Diodes' products are provided subject to Diodes' Standard Terms and Conditions of Sale (https://www.diodes.com/about/company/terms-and-conditions/terms-and-conditions-of-sales/) or other applicable terms. This document does not alter or expand the applicable warranties provided by Diodes. Diodes does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.

6. Diodes' products and technology may not be used for or incorporated into any products or systems whose manufacture, use or sale is prohibited under any applicable laws and regulations. Should customers or users use Diodes' products in contravention of any applicable laws or regulations, or for any unintended or unauthorized application, customers and users will (a) be solely responsible for any damages, losses or penalties arising in connection therewith or as a result thereof, and (b) indemnify and hold Diodes and its representatives and agents harmless against any and all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim relating to any noncompliance with the applicable laws and regulations, as well as any unintended or unauthorized application.

7. While efforts have been made to ensure the information contained in this document is accurate, complete and current, it may contain technical inaccuracies, omissions and typographical errors. Diodes does not warrant that information contained in this document is error-free and Diodes is under no obligation to update or otherwise correct this information. Notwithstanding the foregoing, Diodes reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes.

8. Any unauthorized copying, modification, distribution, transmission, display or other use of this document (or any portion hereof) is prohibited. Diodes assumes no responsibility for any losses incurred by the customers or users or any third parties arising from any such unauthorized use.

9. This Notice may be periodically updated with the most recent version available at https://www.diodes.com/about/company/terms-and-conditions/important-notice

www.diodes.com